

(Use several sheets if necessary)

YOR9-2000-0174

09/612,260

Cohen et al

July 7, 2000

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<p>OK</p>	<p>Wong, et al., "SELF-ALIGNED (TOP AND BOTTOM) DOUBLE-GATE MOSFET WITH A 25 nm THICK SILICON CHANNEL", Electron Devices Meeting, 1997, Technical Digest, International, 1997, pp. 427-430</p>
<p>OK</p>	<p>Lee et al., "SUPER SELF-ALIGNED DOUBLE-GATE (SSDG) MOSFETs UTILIZING OXIDATION RATE DIFFERENCE AND SELECTIVE EPITAXY", IEDM, December 5, 1999, IEEE, 1999</p>

Donghee Kang

8-10-01

SHEET 1 OF 2

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

YOTR9-2000-017

Application Number

09/612,260

Applicant(s)

Cohen et al.

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Group Art Unit

2811

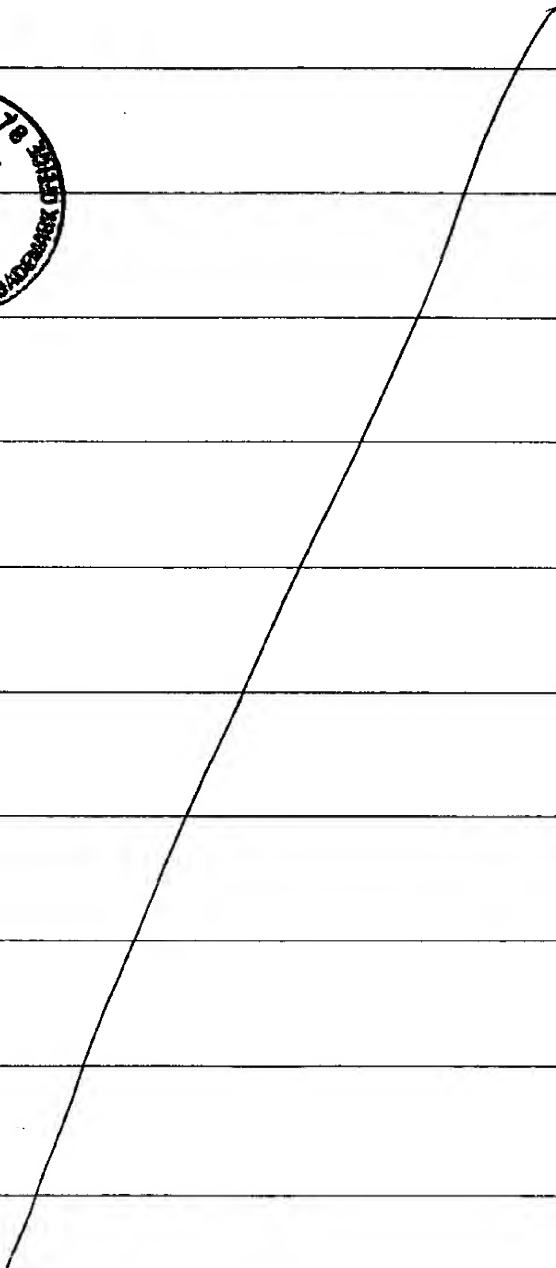
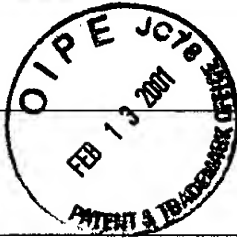
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INITIAL

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

DNH

Su et al., "NEW PLANAR SELF-ALIGNED DOUBLE-GATE FULLY-DEPLETED P-MOSFET's USING EPITAXIAL LATERAL OVERGROWTH (ELO) AND SELECTIVELY GROWN SOURCE/DRAIN (S/D), IEEE SOI Conference, October, 2000



EXAMINER

Donghee Kang

DATE CONSIDERED

8-16-01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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YOR9-2000-01,4

09/612,260

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Donghee Kang

F-10-01

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